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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

Faquir JAIN and Fotios PAPADIMITRAKOPOULIS

Art unit: 1774

Serial No. 09/547,415

Filed: April 11, 2000

For: FULL COLOR DISPLAY STRUCTURE USING CNC THIN FILM
AMENDMENT (clear copy)

Commissioner of Patents
Washington, D.C. 20231

Sir:

In response to USPTO Action dated Jan. 30, 2002, please amend the application as follows:

REFERENCES:

Please delete the list references on page 22.

IN THE DRAWINGS:

Please add reference number "15" in Figure 2(a) as attached.

IN THE SPECIFICATION:

On page 2, line 15, delete "(30" and insert therefor --"3"--.

IN THE CLAIMS:

Please rewrite claims 1, 3, 5-8, 10, 12 and 44 as follows:

1 (once amended) A *p-n* junction electroluminescent (EL) device, comprising successive multiple layers of:

- a semiconductor-on-insulator substrate;
- a *p*-doped Si layer grown on the said substrate, part of the layer being oxidized to isolate the electrodes at the bottom of said device;
- a thin layer of Si relative to the substrate which allows further epitaxial growth;
- a *p*-doped wide energy gap relative to the cladded nanocrystals (CNCs) semiconductor layer grown epitaxially;
- a layer comprising pseudomorphic cladded quantum dots nanocrystals (CNCs) deposited on the said wide energy gap layer for lattice-matched electroluminescence;
- a thin wide energy gap relative to the cladded quantum dot nanocrystals (CNCs) semiconductor layer relative to the substrate having n-type conductivity, grown on the CNC layer; and